

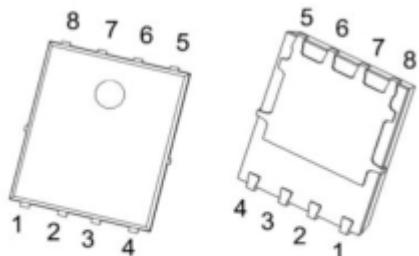
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-40V	4.3mΩ@-10V	-110A
	5.9mΩ@-4.5V	

Feature

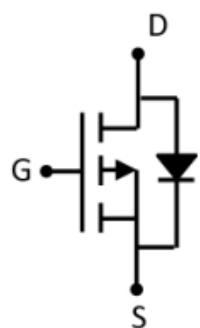
- High Power and current handing capability
- Low on-resistance RDS(on)
- Pb-free lead plating; RoHS compliant

Package

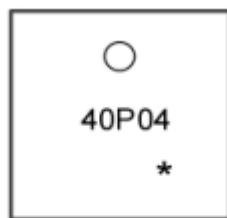


PDFN5×6-8L

Circuit diagram



Marking



40P04 =Device Code
* =Month Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_C=25^\circ\text{C}$)	I_D	-110	A
Drain Current-Pulsed ¹	I_{DM}	-440	A
Single Pulse Avalanche Energy ²	E_{AS}	809	mJ
Maximum Power Dissipation($T_C = 25^\circ\text{C}$)	P_D	73	W
Thermal Resistance, Junction-to-Case	$R_{\Theta JC}$	1.71	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

Electrical characteristics

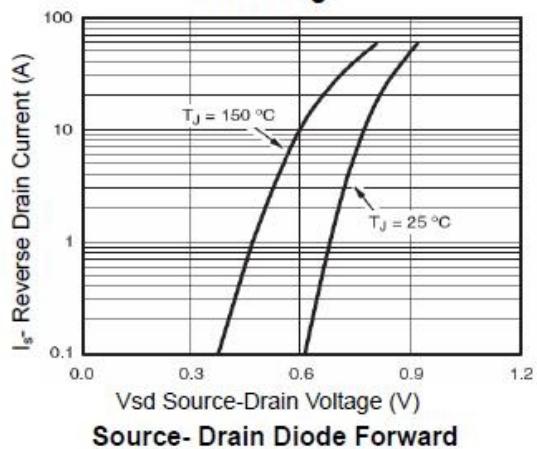
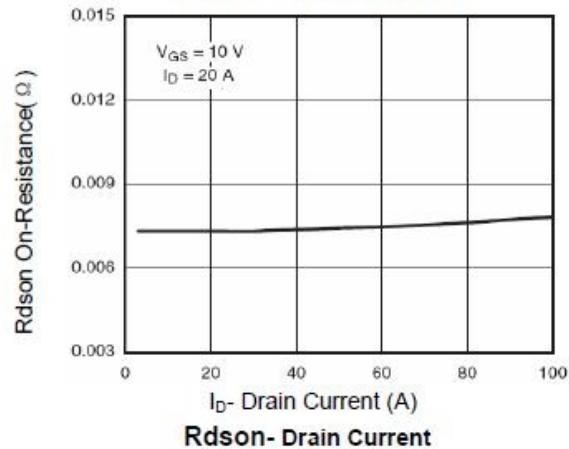
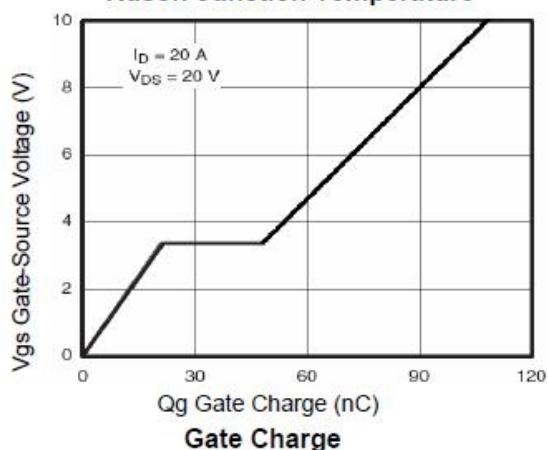
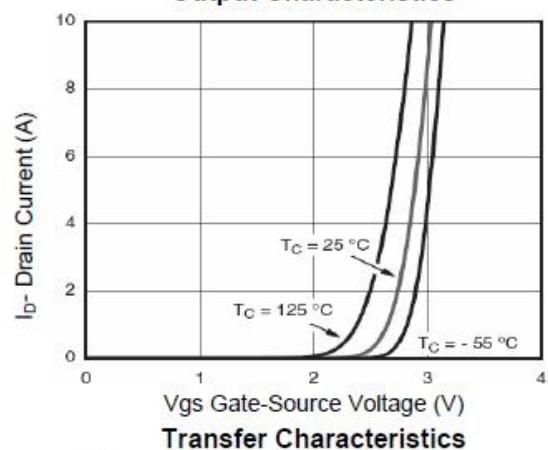
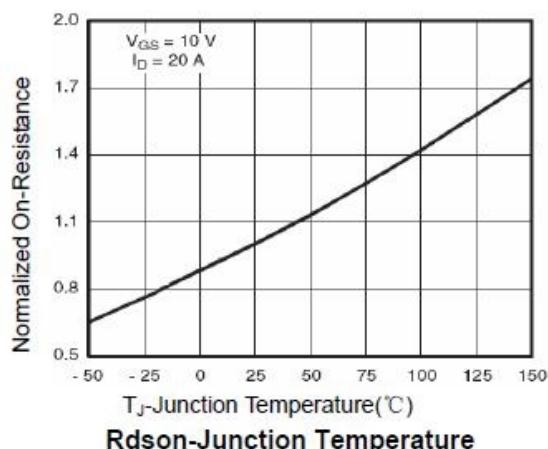
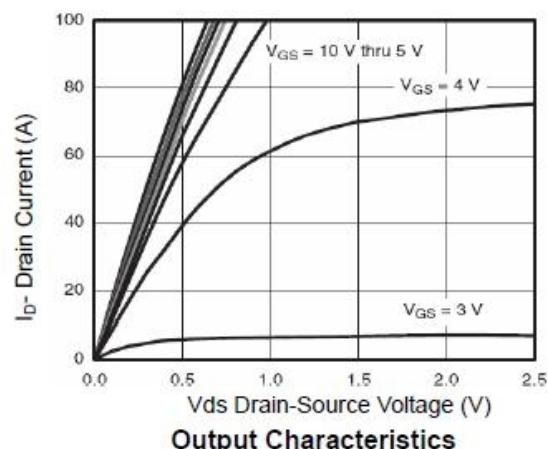
($T_A=25^\circ\text{C}$, unless otherwise noted)

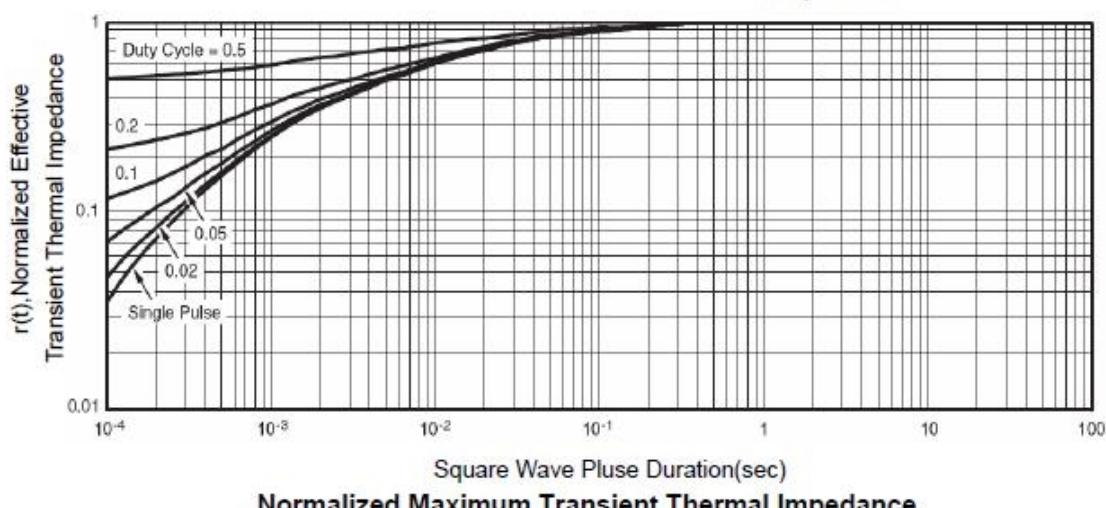
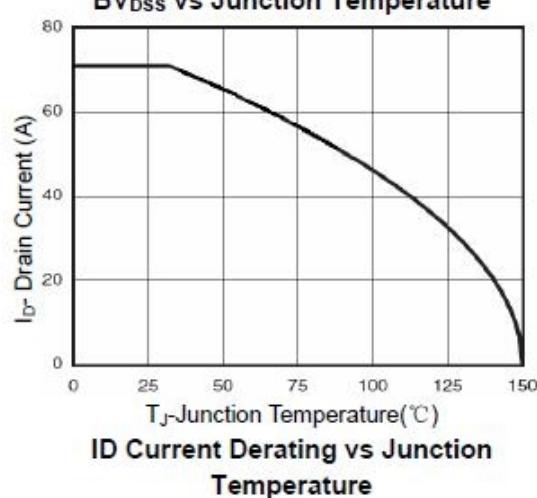
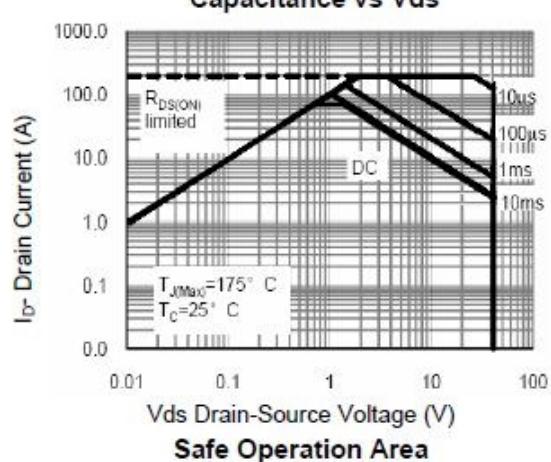
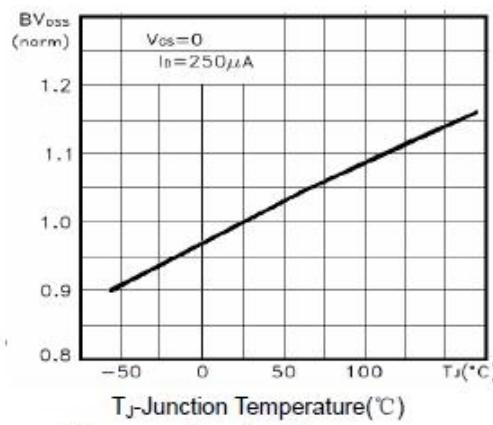
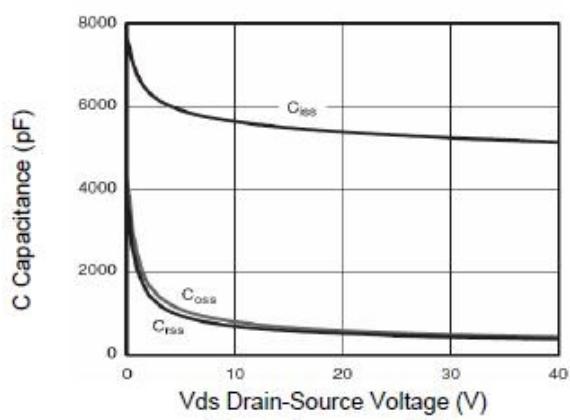
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -32\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.7	-2.5	V
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS} = -10\text{V}, I_D = -20\text{A}$		4.3	5.5	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -20\text{A}$		5.9	8	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=-20\text{V}, f=1\text{MHz}$		7010		pF
Output Capacitance	C_{oss}			640		
Reverse Transfer Capacitance	C_{rss}			450		
Switching Characteristics						
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -20\text{V}, I_D = -20\text{A}$ $V_{GS} = -10\text{V}, R_{GEN} = 2.4\Omega$		10		nS
Turn-on Rise Time	T_r			15		
Turn-off Delay Time	$T_{d(off)}$			93		
Turn-off Fall Time	T_f			20		
Total Gate Charge	Q_g	$V_{DS} = -20\text{V}, I_D = -20\text{A}$ $V_{GS} = -10\text{V}$		74		nC
Gate-Source Charge	Q_{gs}			22		
Gate-Drain Charge	Q_{gd}			18		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{V}, I_s = -2\text{A}$			-1.2	V

Note:

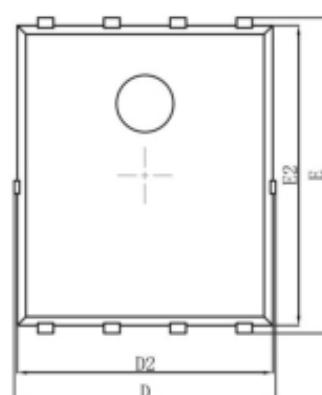
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. E_{AS} data shows Max. rating . The test condition is $V_{DD} = -20\text{V}, V_{GS} = -10\text{V}, L = 0.5\text{mH}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Characteristics

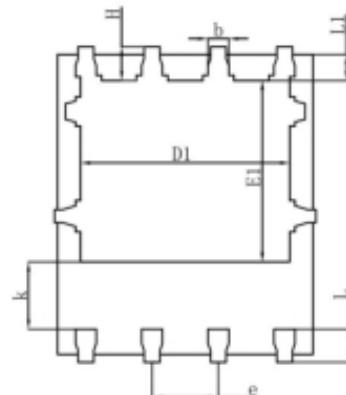




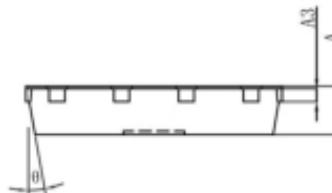
PDFN5×6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.			0.010REF.
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°		12°	